

N-Channel Enhancement-Mode Vertical DMOS FET

Features

- Free from Secondary Breakdown
- Low Power Drive Requirement
- Ease of Paralleling
- Low C_{ISS} and Fast Switching Speeds
- Excellent Thermal Stability
- Integral Source-Drain Diode
- High Input Impedance and High Gain

Applications

- Motor Controls
- Converters
- Amplifiers
- Switches
- Power Supply Circuits
- Drivers (Relays, Hammers, Solenoids, Lamps, Memories, Displays, Bipolar Transistors, etc.)

General Description

The 2N7002 is a low-threshold, Enhancement-mode (normally-off) transistor that uses a vertical DMOS structure and a well-proven silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally induced secondary breakdown.

Microchip's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance and fast switching speeds are desired.

Package Type



See [Table 3-1](#) for pin information.

2N7002

1.0 ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings†

Drain-to-Source Voltage	BV_{DSS}
Drain-to-Gate Voltage	BV_{DGS}
Gate-to-Source Voltage	$\pm 30V$
Operating Ambient Temperature, T_A	$-55^{\circ}C$ to $+150^{\circ}C$
Storage Temperature, T_S	$-55^{\circ}C$ to $+150^{\circ}C$

† **Notice:** Stresses above those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at those or any other conditions above those indicated in the operational sections of this specification is not intended. Exposure to maximum rating conditions for extended periods may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

Electrical Specifications: $T_A = 25^{\circ}C$ unless otherwise specified. (Note 1)						
Parameter	Sym.	Min.	Typ.	Max.	Unit	Conditions
Drain-to-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	$V_{GS} = 0V, I_D = 10 \mu A$
Gate Threshold Voltage	$V_{GS(th)}$	1	—	2.5	V	$V_{GS} = V_{DS}, I_D = 250 \mu A$
Change in $V_{GS(th)}$ with Temperature	$\Delta V_{GS(th)}$	—	—	-5.5	mV/ $^{\circ}C$	$V_{GS} = V_{DS}, I_D = 250 \mu A$ (Note 2)
Gate Body Leakage Current	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
Zero-Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	$V_{GS} = 0V, V_{DS} = \text{Maximum Rating}$
		—	—	500		$V_{GS} = 0V, V_{DS} = 0.8 \text{ Maximum Rating}, T_A = 125^{\circ}C$ (Note 2)
On-State Drain Current	$I_{D(ON)}$	500	—	—	mA	$V_{GS} = 10V, V_{DS} = 25V$
Static Drain-to-Source On-State Resistance	$R_{DS(ON)}$	—	—	7.5	Ω	$V_{GS} = 5V, I_D = 50 \text{ mA}$
		—	—	7.5		$V_{GS} = 10V, I_D = 500 \text{ mA}$
Change in $R_{DS(ON)}$ with Temperature	$\Delta R_{DS(ON)}$	—	—	1	%/ $^{\circ}C$	$V_{GS} = 10V, I_D = 500 \text{ mA}$ (Note 2)

Note 1: All DC parameters are 100% tested at $25^{\circ}C$ unless otherwise stated.
(Pulse test: 300 μs pulse, 2% duty cycle)

2: Specification is obtained by characterization and is not 100% tested.

AC ELECTRICAL CHARACTERISTICS

Electrical Specifications: $T_A = 25^\circ\text{C}$ unless otherwise specified. (Note 2)						
Parameter	Sym.	Min.	Typ.	Max.	Unit	Conditions
Forward Transconductance	G_{FS}	80	—	—	mmho	$V_{DS} = 25\text{V}$, $I_D = 500\text{ mA}$
Input Capacitance	C_{ISS}	—	—	50	pF	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{ MHz}$
Common Source Output Capacitance	C_{OSS}	—	—	25		
Reverse Transfer Capacitance	C_{RSS}	—	—	5		
Turn-On Time	$t_{(ON)}$	—	—	20	ns	$V_{DD} = 30\text{V}$, $I_D = 200\text{ mA}$, $R_{GEN} = 25\Omega$
Turn-Off Time	$t_{(OFF)}$	—	—	20		
DIODE PARAMETER (Note 2)						
Diode Forward Voltage Drop	V_{SD}	—	1.2	—	V	$V_{GS} = 0\text{V}$, $I_{SD} = 200\text{ mA}$ (Note 1)
Reverse Recovery Time	t_{rr}	—	400	—	ns	$V_{GS} = 0\text{V}$, $I_{SD} = 800\text{ mA}$

Note 1: All DC parameters are 100% tested at 25°C unless otherwise stated.
(Pulse test: 300 μs pulse, 2% duty cycle)

2: Specification is obtained by characterization and is not 100% tested.

TEMPERATURE SPECIFICATIONS

Parameter	Sym.	Min.	Typ.	Max.	Unit	Conditions
TEMPERATURE RANGE						
Operating Ambient Temperature	T_A	-55	—	+150	$^\circ\text{C}$	
Storage Temperature	T_S	-55	—	+150	$^\circ\text{C}$	
PACKAGE THERMAL RESISTANCE						
3-lead SOT-23	θ_{JA}	—	203	—	$^\circ\text{C/W}$	

THERMAL CHARACTERISTICS

Package	I_D (Note 1) (Continuous) (mA)	I_D (Pulsed) (mA)	Power Dissipation at $T_A = 25^\circ\text{C}$ (W)	I_{DR} (Note 1) (mA)	I_{DRM} (mA)
3-lead SOT-23	115	800	0.36	115	800

Note 1: I_D (continuous) is limited by maximum T_J .

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2.0 TYPICAL PERFORMANCE CURVES

Note: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g. outside specified power supply range) and therefore outside the warranted range.

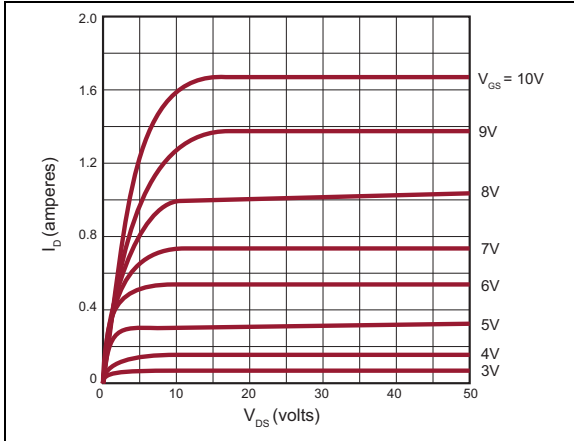


FIGURE 2-1: Output Characteristics.

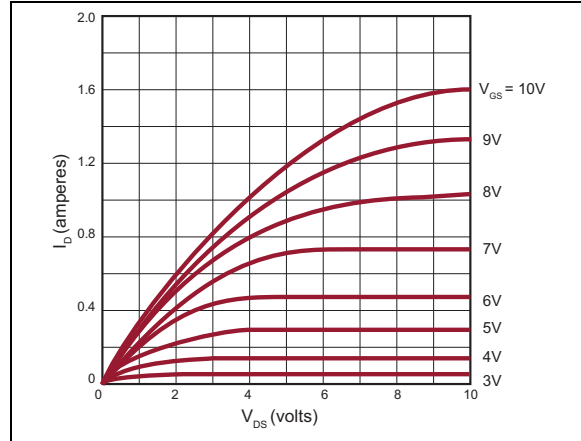


FIGURE 2-4: Saturation Characteristics.

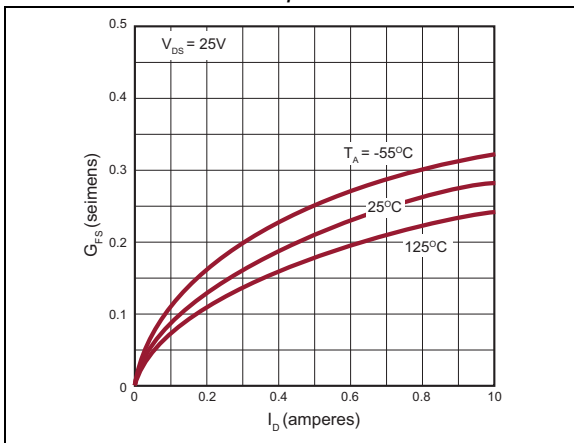


FIGURE 2-2: Transconductance vs. Drain Current.

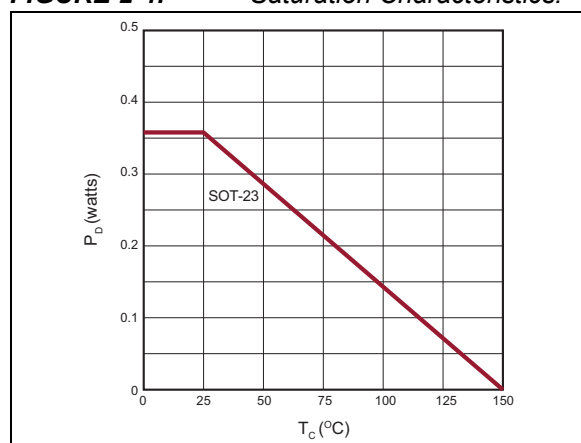


FIGURE 2-5: Power Dissipation vs. Case Temperature.

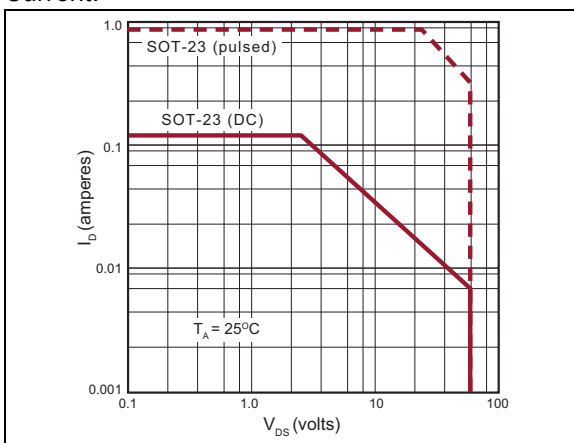


FIGURE 2-3: Maximum Rated Safe Operating Area.

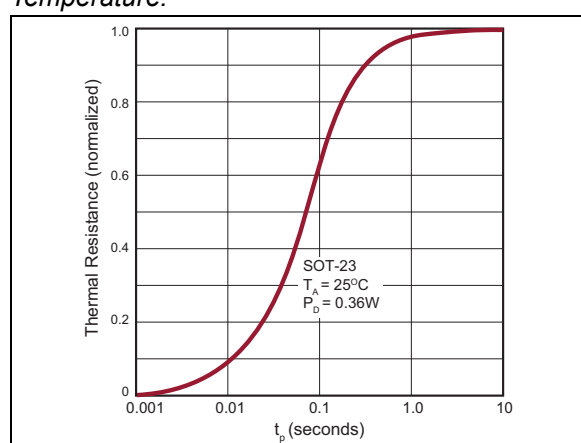


FIGURE 2-6: Thermal Response Characteristics.

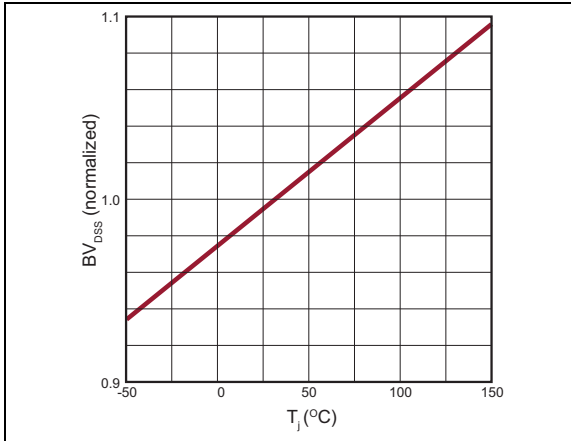


FIGURE 2-7: BV_{DSS} Variation with Temperature.

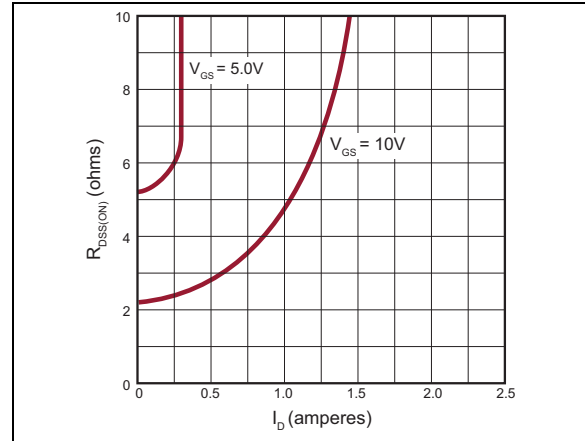


FIGURE 2-10: On-Resistance vs. Drain Current.

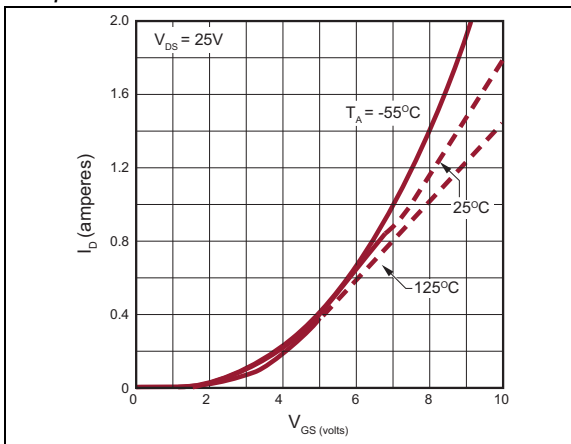


FIGURE 2-8: Transfer Characteristics.

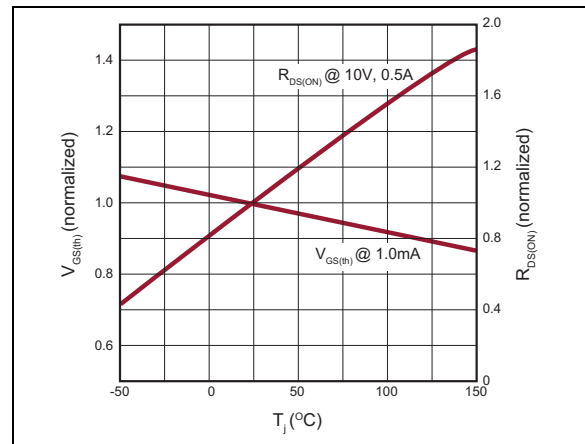


FIGURE 2-11: $V_{GS(th)}$ and $R_{DS(ON)}$ Variation with Temperature.

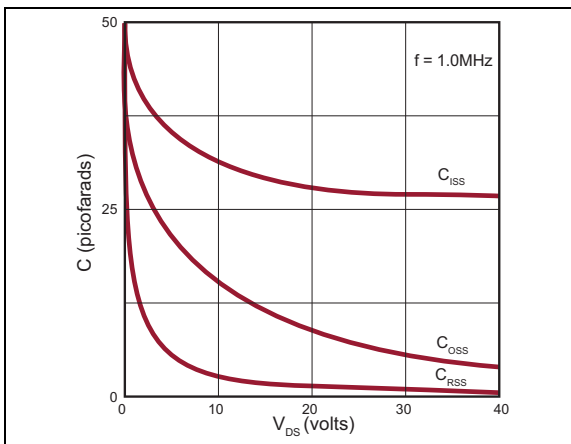


FIGURE 2-9: Capacitance vs. Drain-to-Source Voltage.

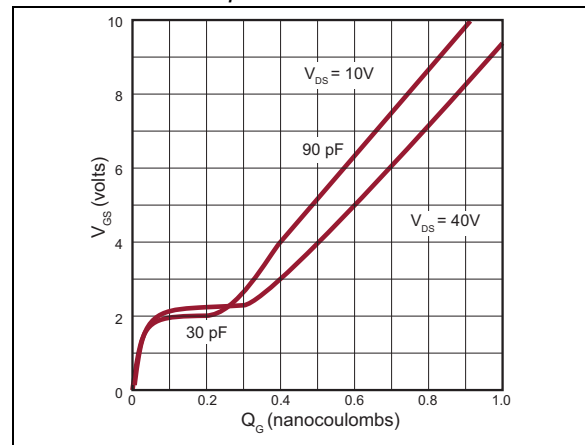


FIGURE 2-12: Gate Drive Dynamic Characteristics.

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3.0 PIN DESCRIPTION

Table 3-1 shows the description of pins in 2N7002.
Refer to [Package Type](#) for the location of pins.

TABLE 3-1: PIN FUNCTION TABLE

Pin Number	Pin Name	Description
1	Gate	Gate
2	Source	Source
3	Drain	Drain

4.0 FUNCTIONAL DESCRIPTION

Figure 4-1 illustrates the switching waveforms and test circuit for 2N7002.

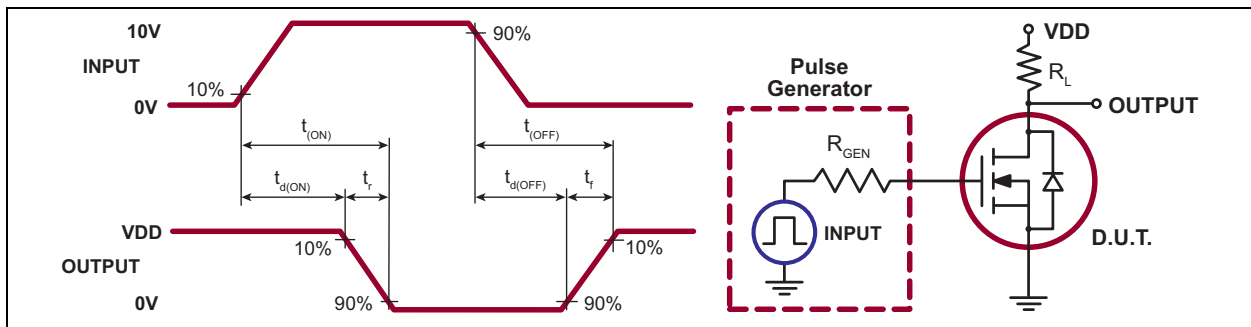


FIGURE 4-1: Switching Waveforms and Test Circuit.

TABLE 4-1: PRODUCT SUMMARY

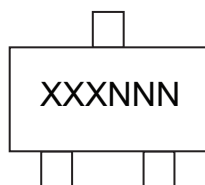
BV_{DSS}/BV_{DGS} (V)	$R_{DS(ON)}$ (Maximum) (Ω)	$I_{D(ON)}$ (Minimum) (mA)
60	7.5	500

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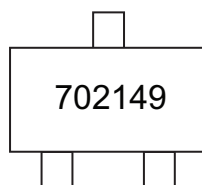
5.0 PACKAGING INFORMATION

5.1 Package Marking Information

3-lead SOT-23

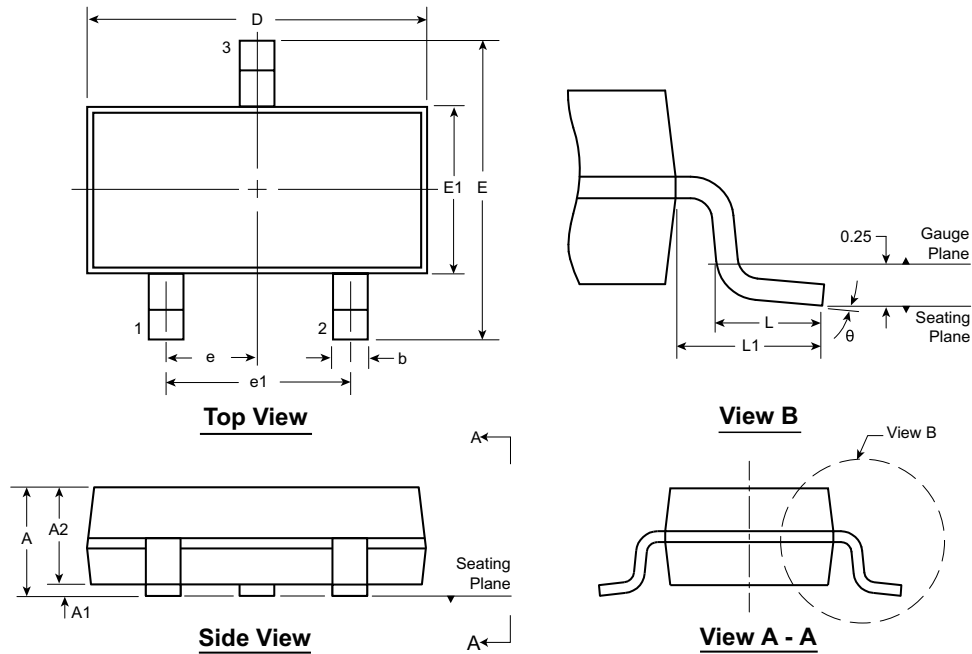


Example



Legend:	XX...X	Product Code or Customer-specific information
	Y	Year code (last digit of calendar year)
	YY	Year code (last 2 digits of calendar year)
	WW	Week code (week of January 1 is week '01')
	NNN	Alphanumeric traceability code
	(e3)	Pb-free JEDEC [®] designator for Matte Tin (Sn)
	*	This package is Pb-free. The Pb-free JEDEC designator (e3) can be found on the outer packaging for this package.
Note:	In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available characters for product code or customer-specific information. Package may or not include the corporate logo.	

3-Lead TO-236AB (SOT-23) Package Outline (K1/T) 2.90x1.30mm body, 1.12mm height (max), 1.90mm pitch



Note: For the most current package drawings, see the Microchip Packaging Specification at www.microchip.com/packaging.

Symbol		A	A1	A2	b	D	E	E1	e	e1	L	L1	θ
Dimension (mm)	MIN	0.89	0.01	0.88	0.30	2.80	2.10	1.20	0.95 BSC	1.90 BSC	0.20 [†]	0.54 REF	0°
	NOM	-	-	0.95	-	2.90	-	1.30			0.50		-
	MAX	1.12	0.10	1.02	0.50	3.04	2.64	1.40			0.60		8°

JEDEC Registration TO-236, Variation AB, Issue H, Jan. 1999.

[†] This dimension differs from the JEDEC drawing.

Drawings not to scale.

2N7002

NOTES:

APPENDIX A: REVISION HISTORY

Revision A (September 2018)

- Converted Supertex Doc# DSFP-2N7002 to Microchip DS20005797A
- Changed the package marking format
- Added some sections to comply with standard Microchip Technology documentation format
- Made minor text changes throughout the document

2N7002

PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, contact your local Microchip representative or sales office.

<u>PART NO.</u>	<u>XX</u>	-	<u>X</u>	-	<u>X</u>
Device	Package Options		Environmental		Media Type
Device:	2N7002	=	N-Channel Enhancement-Mode Vertical DMOS FET		
Package:	(blank)	=	3-lead SOT-23		
Environmental:	G	=	Lead (Pb)-free/RoHS-compliant Package		
Media Type:	(blank)	=	3000/Reel for an SOT-23 Package		

Example:

a) 2N7002-G: N-Channel Enhancement-Mode Vertical DMOS FET, 3-lead SOT-23, 3000/Reel

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